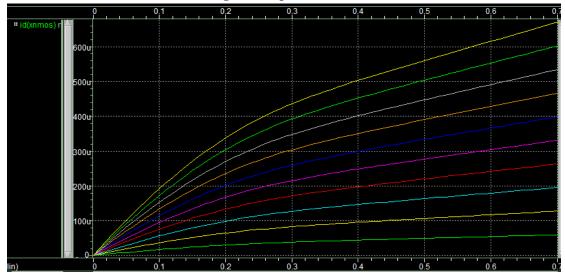
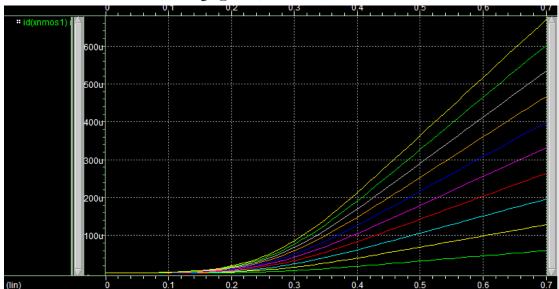
1、IV 曲线展示

n-channel bulk Si-MOSFET, Ids-Vds @25°C, Vgs=0.7V, width=3λ-30λ:



n-channel bulk Si-MOSFET, Ids-Vgs @25°C, Vds=0.7V, width=3λ-30λ:



2、测量数据表格

Measure@25°C, n-channel bulk Si-MOSFET:

Width	3λ	6λ	9λ	12λ	15λ
Ion (uA)	59.83 (示例				
	数据,建议数				
	据保留两位				
	小数)				
I _{off} (nA)	18.22				
I_{on}/I_{off} (x10 ³)	3.28				
$R_{on}/R_{off}(x10^3)$					
Subthreshold					
Slope					
(mV/dec)					

Measure@25°C, p-channel bulk Si-MOSFET:

Width	3λ	6λ	9λ	12λ	15λ
Ion (uA)					
I _{off} (nA)					
I_{on}/I_{off} (x10 ³)					
$R_{on}/R_{off}(x10^3)$					
Subthreshold					
Slope					
(mV/dec)					

Measure@25°C, n-channel FinFET:

1/16d8d16@28 C,					
Fin number	1	2	3	4	5
W _{eff} (nm)					
Ion (uA)					
I _{off} (nA)					
I_{on}/I_{off} (x10 ³)					
Ron/Roff					
Subthreshold					
Slope					
(mV/dec)					
()					
Width	6	7	8	9	10
	6	7	8	9	10
Width	6	7	8	9	10
Width Weff (nm)	6	7	8	9	10
Width Weff (nm) Ion (uA)	6	7	8	9	10
Width Weff (nm) Ion (uA) Ioff (nA)	6	7	8	9	10
$Width$ $W_{eff} (nm)$ $I_{on} (uA)$ $I_{off} (nA)$ $I_{on}/I_{off} (x10^3)$	6	7	8	9	10
$\begin{aligned} & \text{Width} \\ & \text{W}_{\text{eff}} \left(\text{nm} \right) \\ & \text{I}_{\text{on}} \left(\text{uA} \right) \\ & \text{I}_{\text{off}} \left(\text{nA} \right) \\ & \text{I}_{\text{on}} / \text{I}_{\text{off}} \left(\text{x} 10^3 \right) \\ & \text{R}_{\text{on}} / \text{R}_{\text{off}} \left(\text{x} 10^3 \right) \end{aligned}$	6	7	8	9	10

Measure@25°C, p-channel FinFET:

Fin number	1	2	3	4	5
W _{eff} (nm)					
Ion (uA)					
I _{off} (nA)					

I_{on}/I_{off} (x10 ³)					
$R_{on}/R_{off}(x10^3)$					
Subthreshold					
Slope					
(mV/dec)					
Width	6	7	8	9	10
W _{eff} (nm)					
Ion (uA)					
I _{off} (nA)					
I_{on}/I_{off} (x10 ³)					
$R_{on}/R_{off}(x10^3)$					
Subthreshold					
Slope					
(mV/dec)					

Measure@25°C, n-channel TFET (Optional):

Width	3λ	6λ	9λ	12λ	15λ
I _{on} (uA)					
I _{off} (nA)					
I_{on}/I_{off} (x10 ³)					
$R_{on}/R_{off}(x10^3)$					
Subthreshold					
Slope					
(mV/dec)					

Measure@25°C, p-channel TFET (Optional):

Width	3λ	6λ	9λ	12λ	15λ
Ion (uA)					
I _{off} (nA)					
I_{on}/I_{off} (x10 ³)					
$R_{on}/R_{off}(x10^3)$					
Subthreshold					
Slope					
(mV/dec)					